

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1.-18. (Canceled)

19. (Previously Presented) A manufacturing method for a semiconductor device comprising:

emitting a first laser beam from a first laser oscillator;

emitting a second laser beam from a second laser oscillator;

passing the first laser beam through a dichroic mirror and reflecting the second laser beam at the dichroic mirror so that the first laser beam and the second laser beam have a same optical axis;

passing the first laser beam and the second laser beam having the same optical axis through a cylindrical achromatic lens so that the first laser beam and the second laser beam have a same beam length on a surface of a semiconductor film;

crystallizing the semiconductor film by irradiating the semiconductor film with the first laser beam and the second laser beam having the same optical axis and the same beam length,

wherein wavelength of the first laser beam is different from that of the second laser beam, and

wherein a focal point of the first laser beam is different from that of the second laser beam.

20.-22. (Canceled)

23. (Original) The method according to claim 19, wherein the semiconductor device is incorporated into an electronic appliance selected from the group consisting of a video camera, a digital camera, a goggle-type display, a navigation system, a car audio, an audio compo, a computer, a game machine, a mobile computer, a mobile phone, a mobile game machine, an electronic book, and an image reproduction device.

24. (Currently Amended) A manufacturing method for a semiconductor device comprising:

- emitting a first laser beam from a first laser oscillator;

- emitting a second laser beam from a second laser oscillator;

- emitting a third laser beam from a third laser oscillator;

- passing the first laser beam through a first dichroic mirror and reflecting the second laser beam at the first dichroic mirror so that the first laser beam and the second laser beam have a same optical axis;

- passing the first laser beam and the second beam having the same optical axis through a second dichroic mirror and reflecting the third laser beam at the second dichroic mirror so that the first laser beam and the second laser beam having the same optical axis and the third laser beam have the same optical axis;

- passing the first laser beam, the second laser beam and the third laser beam having the same optical axis through a cylindrical [[achromatic]] apochromatic lens so that the first laser beam, the second laser beam and the third laser beam have a same beam length on a surface of a semiconductor film;

- crystallizing the semiconductor film by irradiating the semiconductor film with the first laser beam, the second laser beam and the third laser beam having the same optical axis and the same beam length,

- wherein wavelengths of the first, second, third laser beams are different from each other, and

wherein a focal point of the first laser beam, that of the second laser beam and that of the third laser beam are different from one another.

25.-27. (Canceled)

28. (Original) The method according to claim 24, wherein the semiconductor device is incorporated into an electronic appliance selected from the group consisting of a video camera, a digital camera, a goggle-type display, a navigation system, a car audio, an audio compo, a computer, a game machine, a mobile computer, a mobile phone, a mobile game machine, an electronic book, and an image reproduction device.

29.-44. (Canceled)

45. (Previously Presented) The method according to claim 19, wherein each of the first laser beam and the second laser beam is a continuous wave laser beam.

46. (Previously Presented) The method according to claim 24, wherein each of the first laser beam, the second laser beam and the third laser beam is a continuous wave laser beam.

47. (Previously Presented) The method according to claim 19, further comprising:

etching the crystallized semiconductor film to form crystallized semiconductor layers having desired shapes;

forming a gate insulating film over the crystallized semiconductor layers;

forming a gate electrode over the gate insulating film.

48. (Previously Presented) The method according to claim 24, further comprising:

etching the crystallized semiconductor film to form crystallized semiconductor layers having desired shapes;

forming a gate insulating film over the crystallized semiconductor layers;

forming a gate electrode over the gate insulating film.